

Memory/Clock Drivers

MH7803/MH8803 two phase oscillator/clock driver

general description

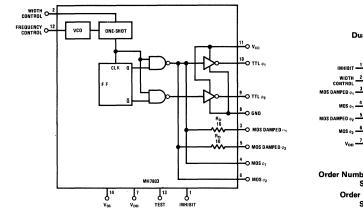
The MH7803 is a self contained two phase oscillator/clock driver. It requires no external components to generate one of three primary oscillator frequencies and pulse widths. Other frequencies can easily be obtained by programming input voltages. Three sets of outputs are provided: damped and un-damped MOS outputs and TTL monitor outputs. The MOS outputs easily drive 500 pF loads with less than 150 ns rise and fall times. In addition the outputs have current limiting to protect against momentary shorts to the supplies.

The MH7803 and MH8803 are available in a 14 lead cavity DIP. The MH8803 is also available in a 14 pin molded DIP.

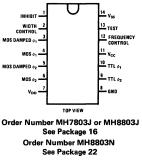
features

- Two phase non-overlapping outputs
- No external timing components required
- Frequency adjustable from 100 kHz to 500 kHz
- Pulse width adjustable from 260 ns to 1.4μ s
- Damped and un-damped MOS outputs
- TTL monitor outputs

block and connection diagrams







absolute maximum ratings

V _{SS} - V _{DD}	22V
V _{CC} – GND	7.0V
Pulse Width Adjust Voltage	V _{SS} + 0.5V
Frequency Adjust Voltage	V _{SS} + 0.5V
V _{SS} – V _{DD} Minimum	14V
Test and Inhibit Input Voltages	V _{SS}

 Operating Temperature Range
 -55°C to +125°C

 MH7803
 0°C to +70°C

 Storage Temperature Range
 -65°C to +150°C

 Lead Temperature (Soldering, 10 seconds)
 300°C

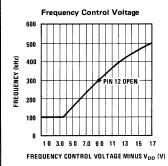
electrical characteristics (Note 1)

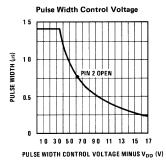
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
Frequency	Pin 12 at 17V, $T_A = 25^{\circ}C$ Pin 12 Open, $T_A = 25^{\circ}C$ Pin 12 at 0V, $T_A = 25^{\circ}C$	300 175 60	500 300 100	600 350 150	kHz kHz kHz	
Frequency Change from 25°C MH7803 MH8803	Pın 12 at 17V Pın 12 at 17V		±20 ±10	±30 ±15	% %	
Pulse Width (Note 2)	Pın 2 at 17V, T _A = 25°C Pın 2 Open, T _A = 25°C Pın 2 at 0V, T _A = 25°C	0 2 0.5 1.0	0.26 0.75 1.4	0.4 1.3 2.6	μs μs μs	
Pulse Width Change from 25°C MH7803 MH8803	Pın 2 at 17V Pın 2 at 17V		±20 ±10	±30 ±15	% %	
MOS V _{OH}	I _{OH} = -100µА	V _{SS} -1 1	V _{SS} -0.8		v	
MOS Vo∟	I _{OL} = 2.0 mA		V _{DD} +0.15	V _{DD} +0.5	v	
TTL V _{он}	I _{OH} = -200µА	2.4	37		v	
TTL V _{OL} MH7803 MH8803	I _{OL} = 2.0 mA I _{OL} = 3 2 mA		0.17 0 2	0.3 0.4	V V	
TTL I _{OS}		3.0	8.0	15	mA	
MOS Output Current Limit			70		mA	
I _{SS}	Pins 2, 12, 13 at 0V, and Pin 1 at −0.3V		10	17	mA	
Icc	Pins 2, 12, at 0V, and Pin 1 at −0.3V		0.75	1.1	mA	
^R D MH7803 MH8803		7.0 5.0	10 10	13 15	Ω Ω	
MOS t _R , t _f	$C_{L} = 500 \text{ pF}, T_{A} = 25^{\circ}\text{C}$ $C_{L} = 50 \text{ pF}, T_{A} = 25^{\circ}\text{C}$		100 20	150 30	ns ns	

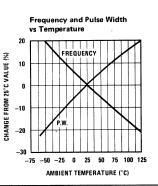
Note 1: These specifications apply for the MH7803 at $V_{SS} - V_{DD}$ = 17V ±10% and over -55°C to +125°C; for the MH8803 at $V_{SS} - V_{DD}$ = 17V ±5% and over 0°C to +70°C unless otherwise specified.

Note 2: The duty cycle can not physically exceed 50% at any output. At high frequencies the frequency adjust pin will affect the pulse width by limiting the duty cycle to slightly less than 50%. Under this condition the pulse width spec does not apply.

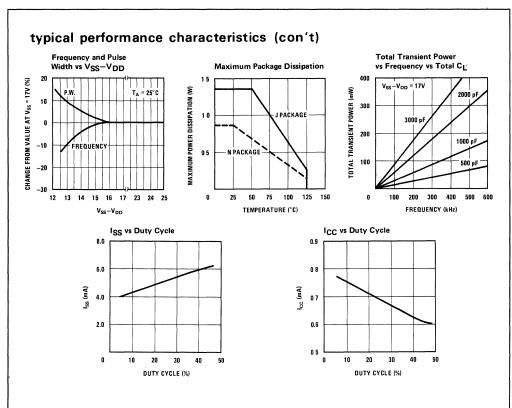
typical performance characteristics







MH7803/MH8803



applications information

TTL MONITOR OUTPUTS

The TTL outputs are extra functions provided for monitor or synchronization applications. In some systems these outputs may not be required. For these cases the V_{CC} pin may be left open and the TTL circuitry power consumption will be virtually zero.

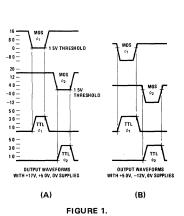
The TTL outputs are slaved to the MOS outputs. Thus the TTL outputs start to switch when the MOS outputs cross the TTL threshold voltage (about 1.5V above ground). Figure 1 depicts the effect of different supply voltages on the TTL waveform when the MOS outputs are driving capacitive loads.

DAMPED MOS OUTPUTS

An extra set of MOS outputs provides a 10 ohm resistor in series with each output line. These resistors give the output pulses an R-C rolloff which tends to minimize ringing or peaking problems associated with board layout.

INHIBIT AND TEST INPUTS

The INHIBIT and TEST inputs are designed to facilitate testing of the device. They were not included in the IC for system use.



Typically they perform as follows:

INHIBIT Input: in the low state prevents pulses r from being initiated on either phase output.

High Level Input:

$$V_{IH} \ge V_{DD} + 2.0V$$

Low Level Input:

$$V_{DD} + 0.2V \ge V_{IL} \ge V_{DD} - 0.5V$$

applications information (con't)

TEST Input: in the low state forces a ONE state on all outputs. The test input should only be used with the INHIBIT input also in the low state.

High Level:

$$V_{IH} \ge V_{DD} + 8.0V$$

Low Level:

 V_{DD} + 0.5V \geq V_{IL} \geq V_{DD}

A pull-up resistor is connected from the TEST pin to $V_{\mbox{\scriptsize SS}}$ internally.

POWER CONSIDERATIONS

Internal power dissipation is affected by three factors:

- dc power
- ac power
- package dissipation capability

The total average power dissipation is the summation of the dc power and ac power. This sum must be less than the maximum package dissipation capability at the particular operating temperature to insure safe operation, i.e.:

$$P_{DISS} = P_{AC} + P_{DC} \le P_{MAX}$$

Where

$$P_{AC} = [(V_{CC} - GND)^2 \times f \times C_L] TTL + [(V_{SS} - V_{DD})^2 \times f \times C_L] MOS$$

And

$$P_{DC} = (I_{CC}) \times (V_{CC} - GND) + (I_{SS})$$
$$\times (V_{SS} - V_{DD})$$

for $I_{\mbox{\scriptsize CC}}$ and $I_{\mbox{\scriptsize SS}}$ selected at the appropriate duty cycle.

For practical cases the $\mathsf{P}_{\mathsf{AC}\ \mathsf{TTL}}$ can be neglected as being very small compared to $\mathsf{P}_{\mathsf{AC}\ \mathsf{MOS}}.$

Thus P_{DISS} is the sum of the MOS transient power (total for both sides of the MH7803) and the standby power of the TTL and MOS sections of the MH7803.

DECOUPLING

It is recommended that each device be decoupled with a $0.1\mu F$ capacitor from V_{SS} to V_{DD} . If there is noise on the supply lines, better frequency and pulse width stability can be obtained by connecting a $0.001\mu F$ capacitor from the frequency control pin to V_{DD} and another $0.001\mu F$ capacitor from the pulse width control pin to V_{DD} .





Memory/Clock Drivers

MH8808 dual high speed MOS clock driver

general description

The MH8808 is a high speed dual MOS clock driver intended to drive the two phases of a memory array of 500 pF per phase at rates up to 4 MHz. The design includes output current limiting for controlled rise and fall times, and thermal shutdown which protects the chip against excessive power dissipation or accidental output shorts. Two DTL/TTL compatible status outputs monitor clock outputs and provide a corresponding TTL logic level for status indication. Both direct and internally damped outputs are available for each phase to suit the particular application. It is ideally suited for driving MM5262 2k RAMs.

features

- High Speed: 18 ns typ delay and 20 ns typ rise and fall times with 500 pF load
- Current limited outputs ±450 mA typ
- Direct and damped outputs available
- Thermal shutdown protection
- TTL compatible status outputs
- 1W dissipation capability at 25°C T_A
- 16 pin cavity dual-in-line package
- Output high level clamped to +5V

